

IN THE CLAIMS:

Claims 1 and 5 have been amended herein. All of the pending claims 1 through 5 are presented below. This listing of claims will replace all prior versions and listings of claims in the application. Please enter these claims as amended.

1. (Currently amended) A semiconductor die having a bond pad arrangement thereon to facilitate packaging thereof, comprising:
a rectangular body having an active surface and a longitudinal centerline; and
a plurality of bond pads disposed adjacent the longitudinal centerline, wherein the plurality of bond pads has a longitudinal length along the longitudinal centerline determined by a longitudinal extent of the plurality of bond pads if equidistantly spaced in a given number of at least one longitudinal row, and wherein the plurality of bond pads are arranged in a same number of longitudinal rows as the given number and comprising at least two longitudinally adjacent groups of bond pads, each bond pad within a group of bond pads being longitudinally separated from adjacent bond pads within the same group of bond pads by an equal interpad spacing of less than an interpad spacing if all of the bond pads of the plurality were equidistantly ~~spaeed~~, spaced, each group of bond pads being separated from at least one longitudinally adjacent group of bond pads by an intergroup spacing of greater than the equal interpad spacing,
wherein a longitudinal length of the at least two groups of bond pads and an intergroup spacing therebetween is substantially the same as the longitudinal length along the longitudinal centerline determined by a longitudinal extent of the plurality of bond pads if equidistantly spaced.
2. (Original) The semiconductor die of claim 1, wherein the at least two longitudinally adjacent groups of bond pads consists of two longitudinally adjacent groups.

3. (Original) The semiconductor die of claim 1, wherein the at least one longitudinal row comprises two longitudinal rows flanking the longitudinal centerline.

4. (Previously presented) The semiconductor die of claim 1, wherein the intergroup spacing is about 1.5 times the interpad spacing.

5. (Currently amended) The semiconductor die of claim 4, wherein the interpad spacing is about 0.4 mm and the ~~intergroup~~ intergroup spacing is about 0.6 mm.